OPTOELECTRONICS DEVICES & INSTRUMENTATION BRANCH : AEIE, EIE, IEE Time : 3 Hours Max Marks : 100 Q.CODE :: E494 Answer Question No.1 (Part-1) which is compulsory, any EIGHT from Part-II and any TWO from Part-III. Part-1 Qart.1 Part-1 Qart.1 Qa	10	210	210	210	210	210	210	210		
Total Number of Pages: 02 B.Tech PEISJ003 200 S ^D Semester Regular / Back Examination 2018-19 OPTOELECTRONICS DEVICES & INSTRUMENTATION BRANCH: AEIE, EIE, IEE Time : 3 Hours Max Marks: 100 Q.CODE: E494 Answer Question No.1 (Part-1) which is compulsory, any EIGHT from Part-II and any TWO from Part-II. 20 210 The figures in the right hand margin indicate marks. 20 211 The figures in the right hand margin indicate marks. 20 212 Short Answer Type Questions (Answer AII-10) (2 x 10) 213 Write various applications of step index fiber and Graded Index fibers. 20 214 Short Answer Type Questions (Answer AII-10) (2 x 10) 215 Write various applications of step index fiber and Graded Index fibers. 20 216 Explain Numerical Aperture (NA) for Graded index fiber. 20 217 Or compare a multimode optical fiber vith single mode optical fiber from application point of view ²¹ (1) Compare a multimode optical dibector? 14.6 219 What is the value of critical angle, numerical aperture and acceptance angle of fiber? 15.0 210 What are the major criteria of semiconductor material selection for optical sources? 16 210 What are the major criteria of semiconductor material selection for optical sources? 16<										
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	k) I)	Explain the detection p the p–i–n photodiode. What are the factors communication?	-		-			
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210	Q4 210	Discuss the operation o i-n photodiode. Enlist the drawbacks a	210	210	ing how it diffe	ers from p- 210	(16)	210
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210	Q6 ₂₁₀ a) b)	Write short notes on OTDR 210 Fiber optic gyroscope		210	210	210	(16)	210
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